

20 V, 4.3 A NPN low VCEsat transistor

20 September 2024

1. General description

NPN low V_{CEsat} transistor in a SOT23 small Surface-Mounted Device (SMD) plastic package. PNP complement: PBSS4021PT-Q

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_CM
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	20	V
I _C	collector current			-	-	4.3	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	8	A
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 4 A; I_{B} = 400 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	32.5	50	mΩ

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	E	emitter		J
3	С	collector		BK E
			1 2 SOT23	sym021

6. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PBSS4021NT-Q		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	<u>SOT23</u>	

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4021NT-Q	%BH

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

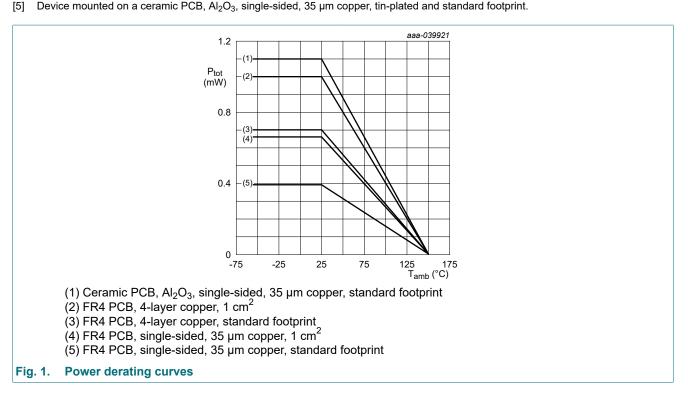
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	20	V
V _{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
l _C	collector current			-	4.3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	А
I _B	base current			-	1	А
P _{tot} total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.39	W	
			[2]	-	0.66	W
			[3]	-	0.7	W
			[4]	-	1	W
			[5]	-	1.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm².
 [5] Device mounted on a ceramic PCB, Al₂O₃, single-sided, 35 µm copper, tin-plated and standard footprint.



9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)} thermal resistance from in free air junction to ambient		in free air	[1]	-	-	320	K/W
	junction to ambient	[2]	-	-	190	K/W	
			[3]	-	-	180	K/W
	[4]	-	-	125	K/W		
		[5]	-	-	115	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	62	K/W

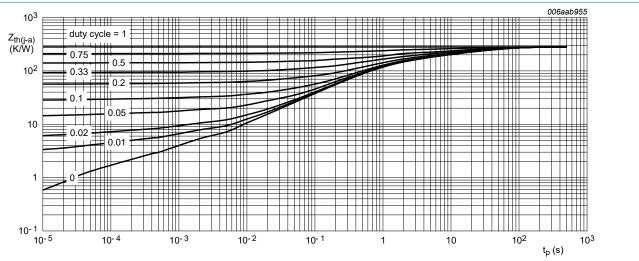
[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

[2] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm²

[3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint

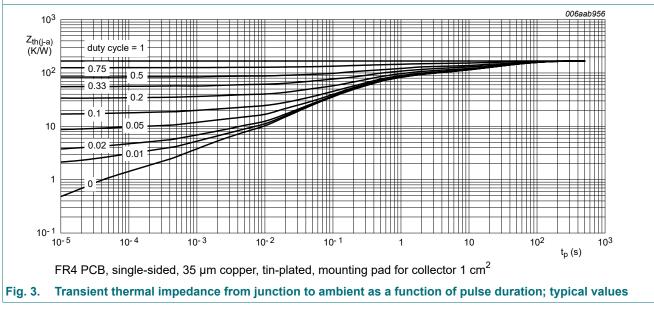
[4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm²

[5] Device mounted on a ceramic PCB, Al₂O₃, single-sided, 35 µm copper, tin-plated and standard footprint

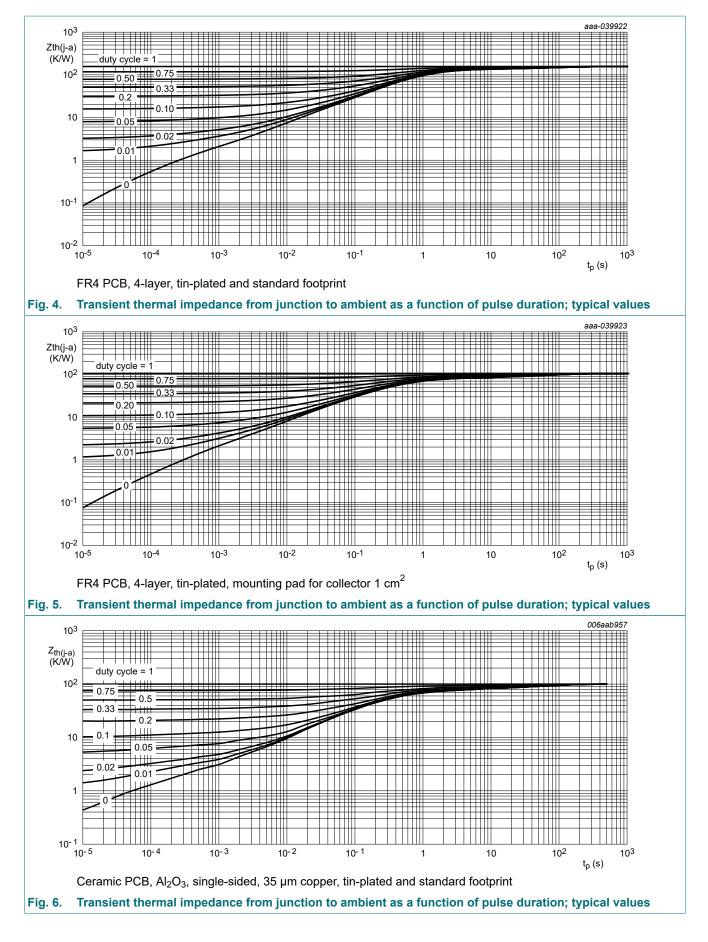


FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint





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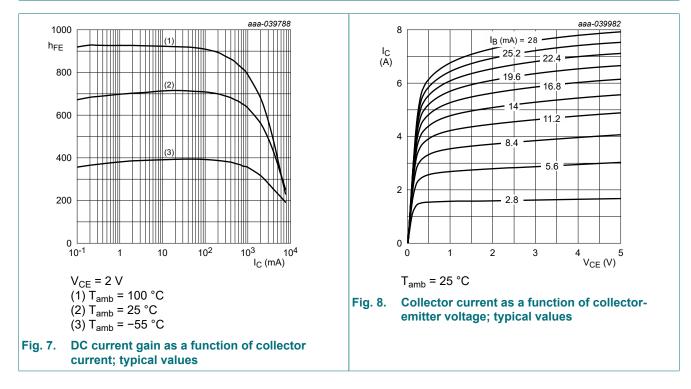
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	I _C = 100 μA; I _E = 0 A; T _{amb} = 25 °C	20	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 10 mA; I _B = 0 A; T _{amb} = 25 °C	20	-	-	V
√ _{(BR)EBO}	emitter-base breakdown voltage	$I_E = 100 \ \mu\text{A}; I_C = 0 \ \text{A}; T_{amb} = 25 \ ^{\circ}\text{C}$	5	-	-	V
I _{CBO} collector-base cut-off		$V_{CB} = 20 \text{ V}; \text{ I}_{\text{E}} = 0 \text{ A}; \text{ T}_{\text{amb}} = 25 ^{\circ}\text{C}$	-	-	100	nA
	current	V _{CB} = 20 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
CES	collector-emitter cut-off current	V_{CE} = 16 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	100	nA
ЕВО	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 500 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	300	600	-	
		V_{CE} = 2 V; I _C = 1 A; pulsed; t _p ≤ 300 µs; $\delta \le 0.02$; T _{amb} = 25 °C	300	550	-	
		$ \begin{array}{l} V_{CE} \texttt{= 2 V; } I_{C} \texttt{= 2 A; pulsed; } t_{p} \texttt{\leq } 300 \ \texttt{\mu s;} \\ \delta \texttt{\leq } 0.02; \ T_{amb} \texttt{= 25 °C} \end{array} $	300	500	-	
		V_{CE} = 2 V; I _C = 4 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	150	400	-	
	V_{CE} = 2 V; I _C = 6 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	100	300	-		
V _{CEsat}	collector-emitter saturation voltage	I _C = 1 A; I _B = 10 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	55	75	mV
		I _C = 1 A; I _B = 50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	40	60	mV
		I _C = 2 A; I _B = 40 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	80	120	mV
		I _C = 4 A; I _B = 40 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	160	265	mV
		I _C = 4 A; I _B = 200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	135	220	mV
		I_{C} = 4 A; I_{B} = 400 mA; pulsed; $t_{p} \le$	-	130	200	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °Ċ	-	32.5	50	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	0.87	1.05	V
		I _C = 4 A; I _B = 400 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	1.08	1.25	V
V _{BE}	base-emitter voltage	V_{CE} = 2 V; I _C = 2 A; pulsed; t _p ≤ 300 µs; $\delta \le 0.02$; T _{amb} = 25 °C	-	0.76	0.9	V

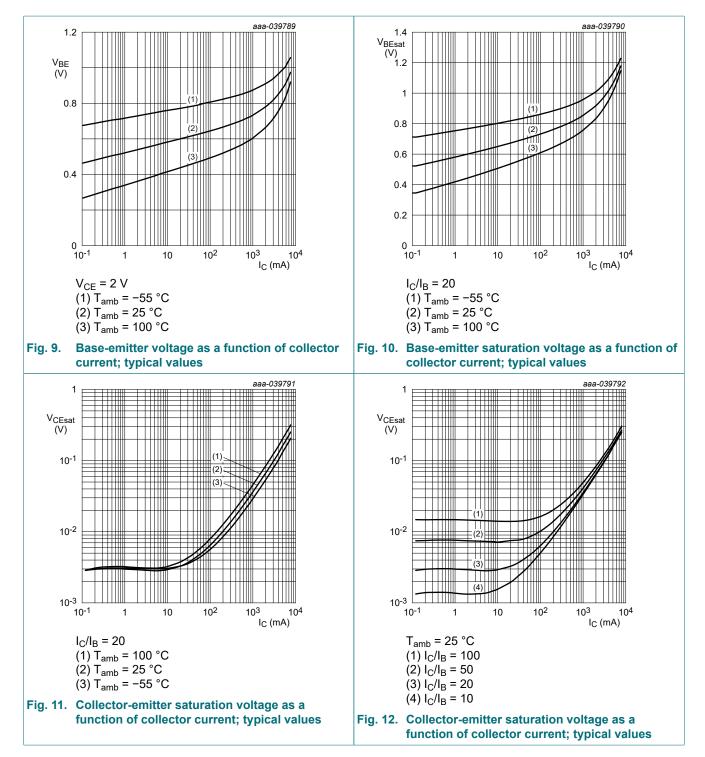
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 50 mA;	-	20	-	ns
t _r	rise time	I _{Boff} = -50 mA; T _{amb} = 25 °C	-	30	-	ns
t _{on}	turn-on time		-	50	-	ns
ts	storage time	_	-	355	-	ns
t _f	fall time		-	70	-	ns
t _{off}	turn-off time	_	-	425	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	-	150	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	36	-	pF

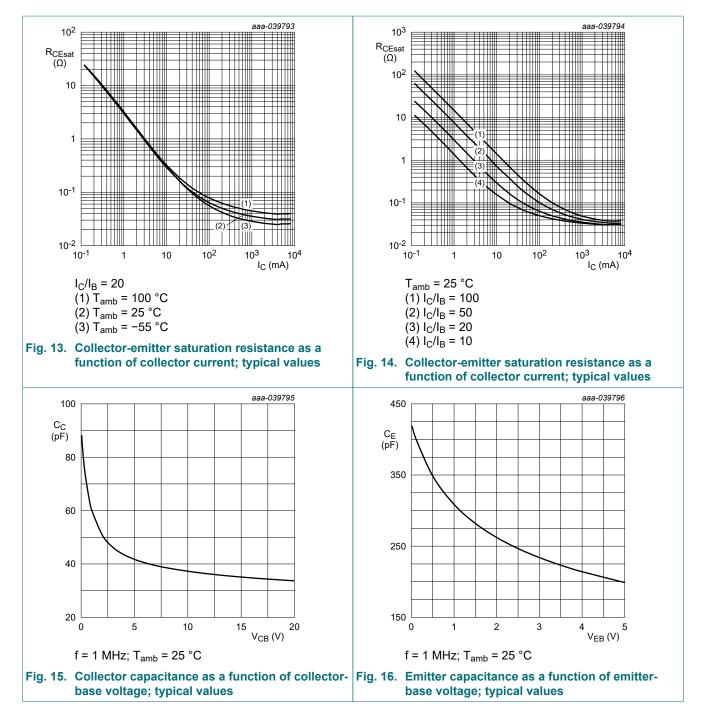


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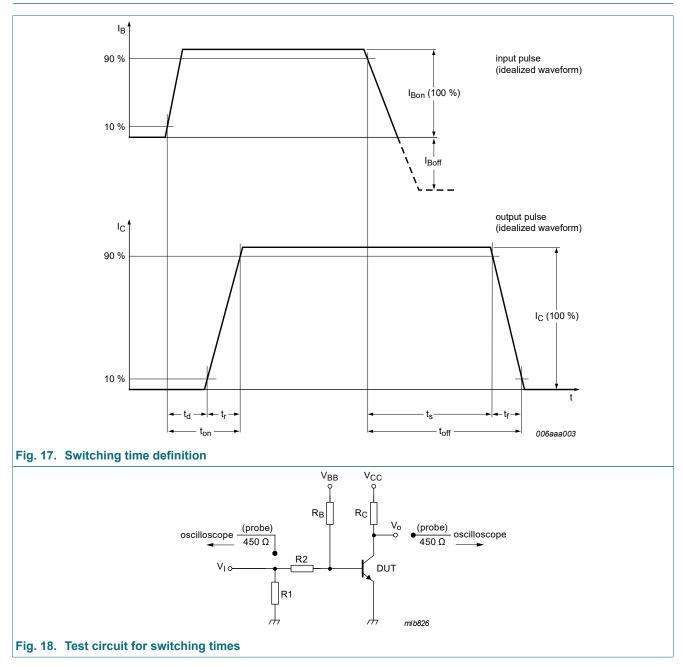
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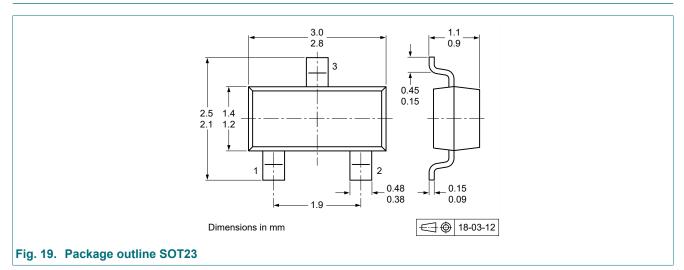
11. Test information



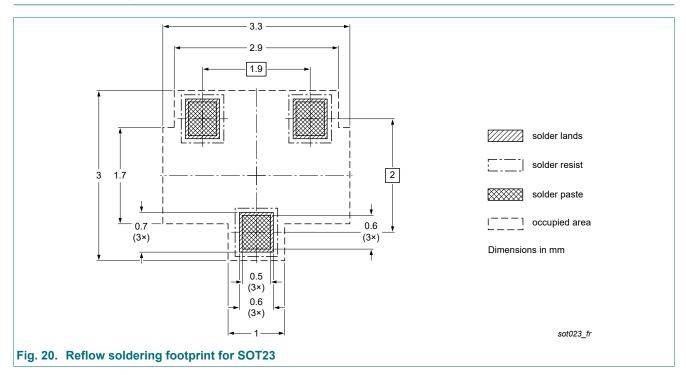
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

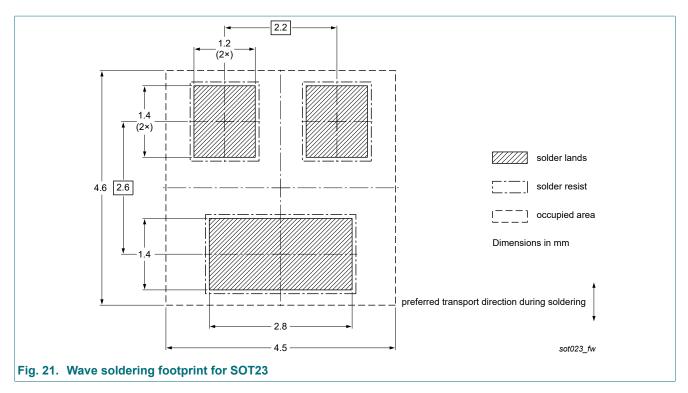
12. Package outline



13. Soldering



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PBSS4021NT-Q

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14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4021NT-Q v.2	20240920	Product data sheet	-	PBSS4021NT-Q v.1		
Modifications:	New graphics added	New graphics added, graphs updated and values changed.				
PBSS4021NT-Q v.1	20240206	Product data sheet	-	-		

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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